

### **KSA1010**

### **High Speed High Voltage Switching**

- Industrial Use
- Complement to KSC2334



1.Base 2.Collector 3.Emitter

### **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 100	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 7	V
I <sub>C</sub>	Collector Current (DC)	- 7	Α
I <sub>CP</sub>	*Collector Current (Pulse)	- 15	Α
I <sub>B</sub>	Base Current	- 3.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	40	W
	Collector Dissipation (T <sub>a</sub> =25°C)	1.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

\* PW≤300μs, Duty Cycle≤10%

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# **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = -5A$ , $I_{B1} = -0.5A$ , $L = 1mH$	- 100		V
V <sub>CEX</sub> (sus)1	Collector-Emitter Sustaining Voltage	$I_C = -5A$ , $I_{B1} = -I_{B2} = -0.5A$ $V_{BE}(off) = 5V$ , $L = 180\mu H$ Clamped	- 100		V
V <sub>CEX</sub> (sus)2	Collector-Emitter Sustaining Voltage	$I_C$ = - 10A, $I_{B1}$ = - 1A $I_{B2}$ = 0.5A, $V_{BE}$ (off) = 5V L = 180 $\mu$ H, Clamped	- 100		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = - 100V, I <sub>E</sub> = 0		- 10	μΑ
I <sub>CER</sub>	Collector Cut-off Current	$V_{CE} = -100V, R_{BE} = 51\Omega$ $T_{C} = 125^{\circ}C$		- 1	mA
I <sub>CEX1</sub>	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$		- 10	μΑ
I <sub>CEX2</sub>	Collector Cut-off Current	$V_{CE} = -100V, V_{BE}(off) = 1.5V$ $T_{C} = 125^{\circ}C$		- 1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$		- 10	uA
h <sub>FE1</sub> h <sub>FE2</sub> h <sub>FE3</sub>	* DC Current Gain	$V_{CE} = -5V, I_{C} = -0.5A$ $V_{CE} = -5V, I_{C} = -3A$ $V_{CE} = -5V, I_{C} = -5A$	40 40 20	200	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> = - 5A, I <sub>B</sub> = - 0.5A		- 0.6	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	I <sub>C</sub> = - 5A, I <sub>B</sub> = - 0.5A		- 1.5	V
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = - 50V, I <sub>C</sub> = - 5A,		0.5	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = -0.5A$		1.5	μs
t <sub>F</sub>	Fall Time	$R_L = 10\Omega$		0.5	μs

Pulse Test: PW≤350μs, Duty Cycle≤2%

### $h_{\mbox{\scriptsize FE}}$ Classification

Classification	R	0	Y
h <sub>FE2</sub>	40 ~ 80	60 ~ 120	100 ~ 200

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## **Typical Characteristics**

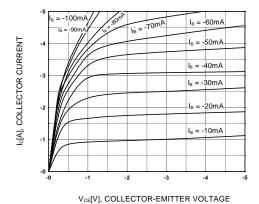


Figure 1. Static Characteristic

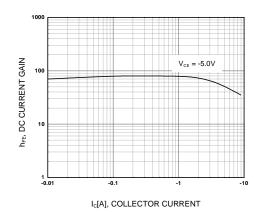


Figure 2. DC current Gain

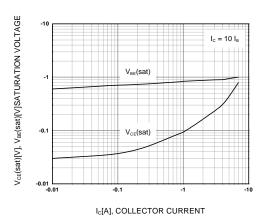


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

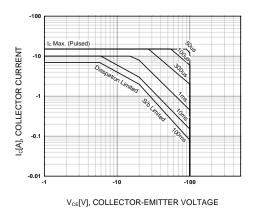


Figure 4. Safe Operating Area

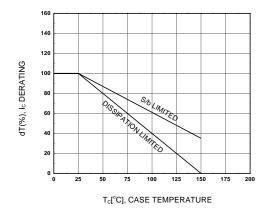


Figure 5. Derating Curve of Safe Operating Areas

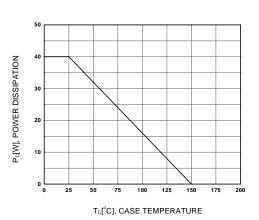


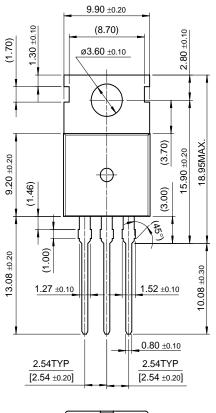
Figure 6. Power Derating

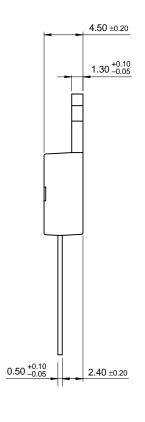
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## **Package Demensions**

## TO-220





10.00 ±0.20

Dimensions in Millimeters

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